

## IEEE EDS Kansai Chapter Award 2009

### ■ IEEE EDS Kansai Chapter IMFEDK Best Paper Award

Titled: *“Influence of Edge Roughness on the Performance of Graphene Nano-Ribbon Devices”*

Authors: **Satofumi Souma**<sup>1</sup>, M. Ogawa<sup>1</sup>, T. Yamamoto<sup>2</sup>, K. Watanabe<sup>3</sup>

Affiliation: <sup>1</sup>Kobe University, <sup>2</sup>The University of Tokyo, <sup>3</sup>Tokyo University of Science

### ■ IEEE EDS Kansai Chapter IMFEDK Student Paper Award

Author: **Hiroki Miyake**

Titled: *“Demonstration of Common-Emitter Mode Operation in AlGaN/SiC Heterojunction Bipolar Transistors”*

Coauthors: T. Kimoto, J. Suda

Affiliation: Kyoto University

Author: **Eri Ogawa**

Titled: *“Effects of High-Temperature Anneal on Surface Properties of Mg-Doped GaN”*

Coauthor: T. Hashizume

Affiliation: Hokkaido University

Author: **Keita Yoshikawa**

Titled: *“Multi-Axis Force Detection Using Piezoelectric Resonant Cantilever Sensors”*

Coauthors: T. Kawata, K. Yamashita, M. Noda

Affiliation: Kyoto Institute of Technology

Author: **Hironori Yoshioka**

Titled: *“One-Dimensional Quantum Confinement Effects in Si-Nanowire MOSFETs”*

Coauthors: N. Moioka, J. Suda, T. Kimoto

Affiliation: Kyoto University

Author: **Kosuke Ohara**<sup>1</sup>

Titled: *“Floating Gate Memory Devices Based on Ferritin Nanodots on High-k Gate Dielectrics”*

Coauthors: Y. Uraoka<sup>1</sup>, T. Fuyuki<sup>1</sup>, I. Yamashita<sup>1</sup>, T. Yaegashi<sup>2</sup>, M. Moniwa<sup>2</sup>, M. Yoshimaru<sup>2</sup>

Affiliation: <sup>1</sup>Nara Institute of Science and Technology, <sup>2</sup>Semiconductor Technology Academic Research Center

Author: **Shunsuke Nakano**<sup>1</sup>

Titled: *“Gate, Source and Drain Engineering for sub-100-nm-Channel Si-Wire Gate-All-Around MOSFET”*

Coauthors: O. Hayashi<sup>1</sup>, Y. Omura<sup>1</sup>, S Yamakawa<sup>2</sup>, H. Wakabayashi<sup>2</sup>

Affiliation: <sup>1</sup>Kansai University, <sup>2</sup>Sony Corp.

■ **IEEE EDS Kansai Chapter of the Year Award**

Author: **Yuichiro Sasaki**<sup>1</sup>

Titled: *“Conformal Doping for FinFETs and Precise Controllable Shallow Doping for Planar FET Manufacturing by a Novel B<sub>2</sub>H<sub>6</sub>/Helium Self-Regulatory Plasma Doping Process”*

Coauthors: K. Okashita<sup>1</sup>, K. Nakamoto<sup>1</sup>, T. Kitaoka<sup>1</sup>, B. Mizuno<sup>1,2</sup>, M. Ogura<sup>2</sup>

Affiliation: <sup>1</sup>Ultimate Junction Technologies Inc., <sup>2</sup>Panasonic Corp.

■ **IEEE EDS Kansai Chapter MSFK Award**

Author: **Ayuta Suzuki**<sup>1</sup>

Titled: *“Molecular Dynamics Simulations of Low-k SiOCH film etching by fluorocarbon plasmas”*

Coauthors: M. Isobe<sup>1</sup>, S. Kobayashi<sup>2</sup>, M. Fkasawa<sup>2</sup>, T. Tatsumi<sup>2</sup>, S. Hamaguchi<sup>2</sup>

Affiliation: <sup>1</sup>Osaka University, <sup>2</sup>Sony Corp.